

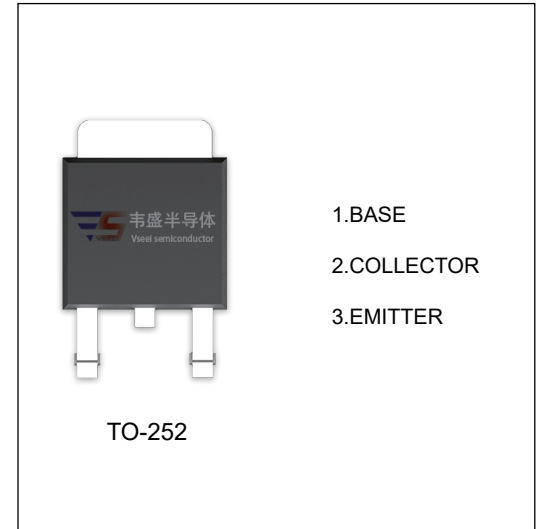
2SB1182 TRANSISTOR (PNP)

FEATURES

- Power Dissipation

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector- Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-32	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-2	A
P _C	Collector Power Dissipation	1.5	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-50μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-32			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-50μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-20V, I _E =0			-1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-1	μA
DC current gain	h _{FE(1)}	V _{CE} =-3V, I _C =-500mA	82		390	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-2A, I _B =-200mA			-0.8	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-0.5A, f=30MHz		100		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		50		pF

CLASSIFICATION OF h_{FE(1)}

Rank	P	Q	R
Range	82-180	120-270	180-390

